

DCR5240H52



Phase Control Thyristor

Preliminary Information

DS6160- 1 September 2014 (LN31988)

FEATURES

- Double Side Cooling
- High Surge Capability

APPLICATIONS

- High Power Drives
- High Voltage Power Supplies
- Static Switches

VOLTAGE RATINGS

Part and Ordering Number	Repetitive Peak Voltages V _{DRM} and V _{RRM} V	Conditions
DCR5240H52* DCR5240H50 DCR5240H48	5200 5000 4800	$\begin{array}{l} T_{vj} = -40^{\circ}C \ to \ 125^{\circ}C, \\ I_{DRM} = I_{RRM} = 600 mA, \\ V_{DRM}, \ V_{RRM} \ t_p = 10 ms, \\ V_{DSM} \& \ V_{RSM} = \\ V_{DRM} \& \ V_{RRM} \ + 100 V \\ respectively \end{array}$

Lower voltage grades available. *5000V @ -40° C, 5200V @ 0° C

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DCR5240H52

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

KEY PARAMETERS

5200V
5240A
77800A
2000V/µs
200A/µs

* Higher dV/dt selections available

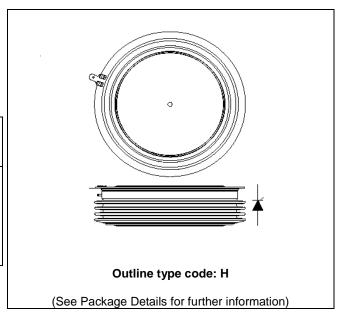


Fig. 1 Package outline





CURRENT RATINGS

 $T_{case} = 60^{\circ}C$ unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Sid	de Cooled			
I _{T(AV)}	Mean on-state current	Half wave resistive load	5240	А
I _{T(RMS)}	RMS value	-	8230	А
Ι _Τ	Continuous (direct) on-state current	-	7290	А

SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
I _{TSM}	Surge (non-repetitive) on-state current	10ms half sine, $T_{case} = 125^{\circ}C$	77.80	kA
l ² t	I ² t for fusing	$V_R = 0$	30.27	MA ² s

THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Condition	s	Min.	Max.	Units
R _{th(j-c)}	Thermal resistance – junction to case	Double side cooled	DC	-	0.004255	°C/W
		Single side cooled	Anode DC	-	0.008	°C/W
			Cathode DC	-	0.0093	°C/W
R _{th(c-h)}	Thermal resistance – case to heatsink	Clamping force 135.0kN	Double side	-	0.0009	°C/W
		(with mounting compound)	Single side	-	0.0018	°C/W
T_{vj}	Virtual junction temperature	Blocking V _{DRM} / V _{RRM}		-	125	°C
T _{stg}	Storage temperature range			-55	125	°C
Fm	Clamping force			120	155	kN





DYNAMIC CHARACTERISTICS

Symbol	Parameter	Test Conditio	ns	Min.	Max.	Units
I _{RRM} /I _{DRM}	Peak reverse and off-state current	At V _{RRM} /V _{DRM} , T _{case} = 125°C		-	600	mA
dV/dt	Max. linear rate of rise of off-state voltage	To 67% V _{DRM} , T _j = 125°C, ga	ate open	-	2000	V/µs
dl/dt	Rate of rise of on-state current	From 67% V_{DRM} to 2x $I_{T(AV)}$	Repetitive 50Hz	-	200	A/µs
		Gate source 30V, 10Ω, t _r < 0.5μs, T _j = 125°C	Non-repetitive	-	500	A/µs
V _{T(TO)}	Threshold voltage – Low level	500 to 4000A at $T_{case} = 125^{\circ}$	С	-	0.975	V
	Threshold voltage – High level	4000 to 8000A at T _{case} = 125	5°C	-	1.222	V
r _T	On-state slope resistance – Low level	500A to 4000A at $T_{case} = 125$	5°C	-	0.175	mΩ
	On-state slope resistance – High level	4000A to 8000A at $T_{case} = 12$	25°C	-	0.118	mΩ
t _{gd}	Delay time	$V_D = 67\% V_{DRM}$, gate source $t_r = 0.5 \mu s$, $T_i = 25^{\circ}C$	30V, 10Ω	-	3	μs
tq	Turn-off time	$I_{T} = 3000A, T_{j} = 125^{\circ}C, \\ V_{R} = 200V, dI/dt = 1A/\mu s, \\ dV_{DR}/dt = 20V/\mu s linear$			500	μs
Qs	Stored charge	I _T = 3000A, T _i = 125°C, dl/dt	– 1A/us	2230	4290	μC
I _{RR}	Reverse recovery current	V _{Rpeak} ~3100V, V _R ~ 2100V		38	52	A
ΙL	Latching current	$T_j = 25^{\circ}C, V_D = 5V$		-	3	A
Iн	Holding current	$T_j = 25^{\circ}C, R_{G-K} = \infty, I_{TM} = 50$	0A, I _T = 5A	-	300	mA





GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
V _{GT}	Gate trigger voltage	$V_{DRM} = 5V, T_{case} = 25^{\circ}C$	1.5	V
V_{GD}	Gate non-trigger voltage	At 50% V _{DRM,} T _{case} = 125°C	0.4	V
I _{GT}	Gate trigger current	$V_{DRM} = 5V, T_{case} = 25^{\circ}C$	350	mA
I _{GD}	Gate non-trigger current	At 50% V _{DRM} , T _{case} = 125°C	10	mA

CURVES

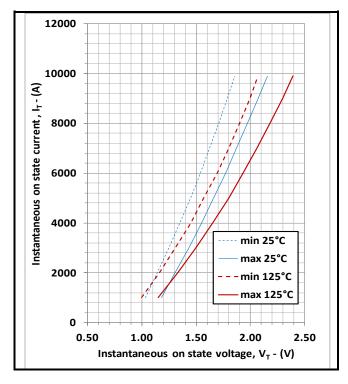


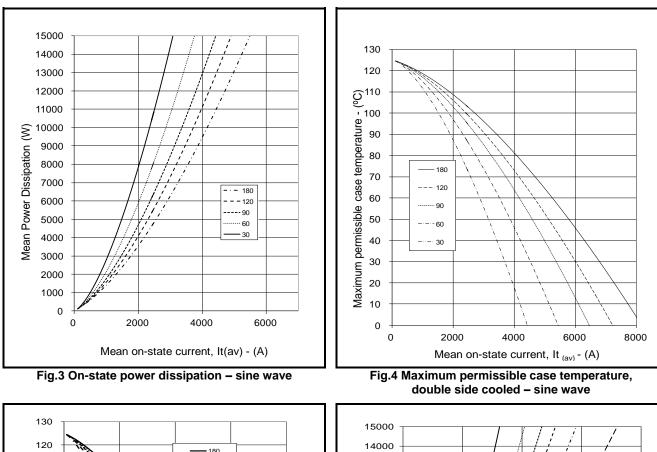
Fig.2 Maximum & minimum on-state characteristics

V_{TM} EQUATION

Where A = 2.0022 B = -0.2464 C = -0.0000027 D = 0.02699 these values are valid for T_j = 125°C for I_T 500A to 8000A

 $V_{TM} =$





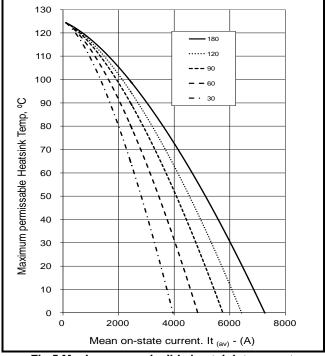


Fig.5 Maximum permissible heatsink temperature, double side cooled – sine wave

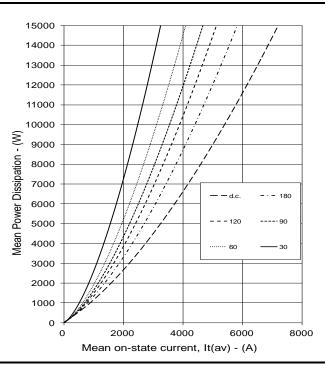
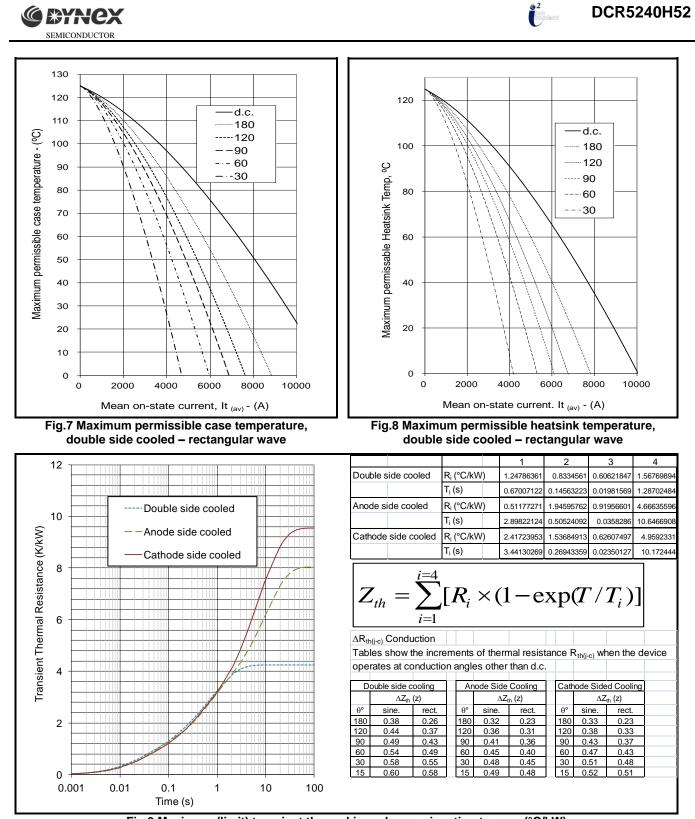
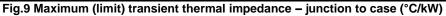


Fig.6 On-state power dissipation – rectangular wave





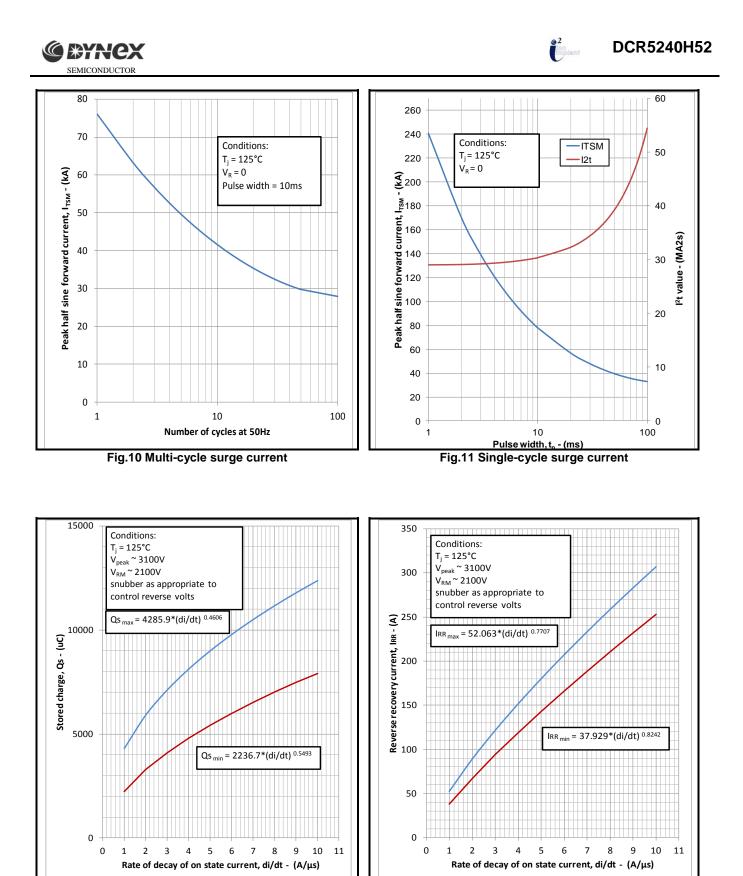
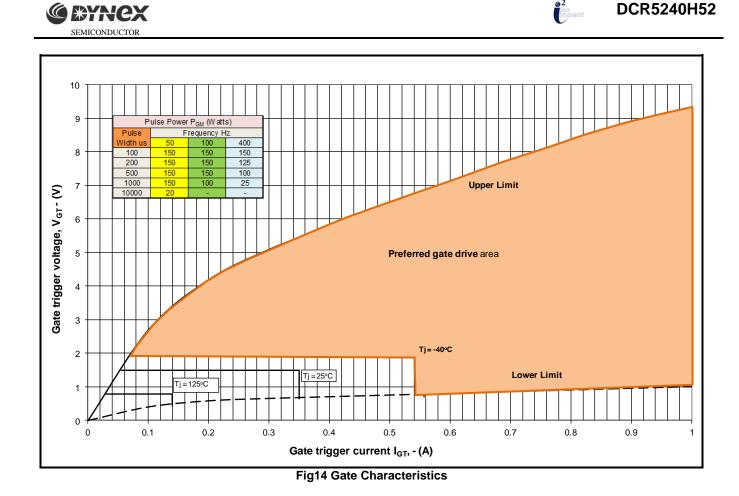


Fig.12 Stored charge

Fig.13 Reverse recovery current



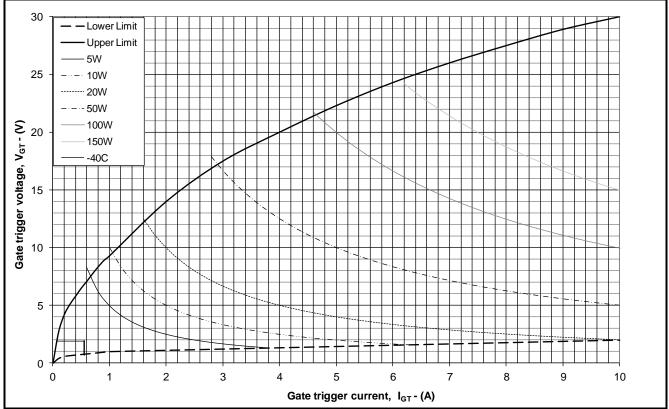


Fig. 15 Gate characteristics



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PACKAGE DETAILS

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.

Thickness Thickness Device (mm) (mm) DCRxxxxH42 35.15 34.28 DCR5240H52 35.27 34.4 DCR5890H52 35.3 34.7 DCR4420H65 35.3 34.7 DCR4660H65 35.3 34.7 DCR3640H85 35.65 35.05 DCR3980H85 35.65 35.05		Maximum	Minimum		
DCRxxxxH42 35.15 34.28 DCR5240H52 35.27 34.4 DCR5890H52 35.27 34.4 DCR4420H65 35.3 34.7 DCR4660H65 35.3 34.7 DCR3640H85 35.65 35.05		Thickness	Thickness		
DCR5240H5235.2734.4DCR5890H5235.2734.4DCR4420H6535.334.7DCR4660H6535.334.7DCR3640H8535.6535.05	Device	(mm)	(mm)		
DCR5890H5235.2734.4DCR4420H6535.334.7DCR4660H6535.334.7DCR3640H8535.6535.05	DCRxxxxH42	35.15	34.28		
DCR4420H6535.334.7DCR4660H6535.334.7DCR3640H8535.6535.05	DCR5240H52	35.27	34.4		
DCR4660H6535.334.7DCR3640H8535.6535.05	DCR5890H52	35.27	34.4		
DCR3640H85 35.65 35.05	DCR4420H65	35.3	34.7		
	DCR4660H65	35.3	34.7		
DCR3980H85 35.65 35.05	DCR3640H85	35.65	35.05		
	DCR3980H85	35.65	35.05		
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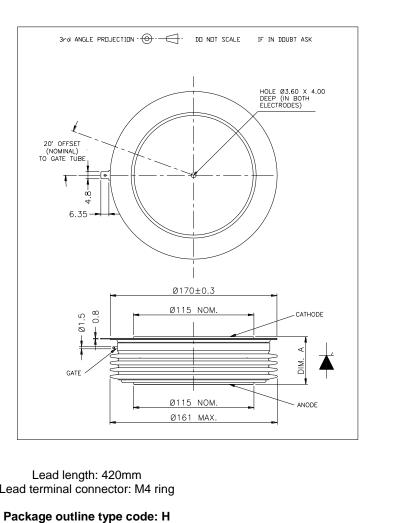
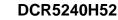


Fig.16 Package outline





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